



# Enhanced Interfacing of Single Element Resistive Sensor with Microcontroller

M. Florance Mary, D. Sathish

**Abstract:** Resistive sensors can be used in a single element, differential and bridge forms. Resistive sensors have wide applications in industries. When the resistive sensor is directly connected with the microcontroller large amount of error arises due to lead wire resistance and microcontroller port pin resistances. Here, an enhanced interfacing of single element resistive sensor with a microcontroller scheme is proposed to compensate the error due to lead wires and port pin resistances. This scheme follows three discharge cycles for the measurement of resistances of the resistive sensor. The time taken for each discharge cycle is noted. From the time taken for the three discharge cycles, the resistance  $R_y$  of the resistive sensor is directly calculated. Since the resistances due to lead wires and internal port pin resistances are corrected, the unknown temperature measurement is done accurately.

**Keywords:** RTD, Single element resistor, Microcontroller.

## I. INTRODUCTION

Resistive sensors are one of the commonly used types of an analog sensor. The resistive sensor converts the physical quantity into variable resistance for the sake of measurement. Resistive sensors are in different forms such as single element, differential, and bridge forms. Single element resistive sensor such as Resistive Temperature Detector (RTD) senses the physical quantity by using one sensing element. Resistive sensors are connected to the measuring unit through some lead wires. These lead wires have some lead wire resistances due to which large amount of error will arise. These lead wire resistances affect the accuracy of the measurement.

Many works are done for accurate measurement of temperature using temperature sensors like RTD, thermocouple, and thermistor. A two-wire method with a self-heating technique for the RTD sensors was used to provide long lead resistance compensation. It was able to compensate for large lead resistance of tens of ohms in a repetitive: time-sharing mode, avoiding its variations with the environmental temperature [1]. The temperature was measured using the RTD along with signal conditioning

circuits, which includes voltage/current excitation, amplification, and linearization. From the comparison, it was found that the four-wire RTD provides good interchangeable configuration and cancels out the lead resistance effectively compared to other RTD wire configuration. This method is not suitable for two-wire and three wire RTDs [2]. A compensation technique was also proposed for three-wire and four-wire RTDs which is not a suitable technique for the single element resistive sensors. Here it was found that the output would be affected by the non-ideal characteristics of the op-amps [3], [4]. A lead wire compensation for two-wire Resistance Temperature Detectors (RTD) having signal conditioning circuits using sample and hold, current source and diodes was also proposed and found to be complex [5].

When considering the interfacing of RTD to the microcontroller, many schemes are proposed. In the multi-point temperature measurement scheme stated for three-wire RTD having lead wire compensation for measurement of temperature, it was found to have complex analog signal conditioning circuits [6]. Op-amp based V-to-I converter was used along with the resistive sensor as a novel remote measurement technique. Here, V-to-I converter needs to be excited by a square wave of 50 % duty cycle [7]. Direct interface circuits can measure different categories of resistive sensors using an 8-bit microcontroller along with internal timer. This technique was found to be feasible for low-value resistive sensors and not for the high-value resistive sensors [8]. A realization technique using an interface circuit for single resistive sensors, that provides an output signal linearly related to resistive sensor was implemented. This scheme needs a separate circuitry for current source [9]. There are few works carried based on discharge cycles. Discharging performed through three different micro-controller port pins was used for measurement and it was found that the accuracy was affected by the mismatch between the port pin resistances as detailed in [10].

The sensor to microcontroller interface with long lead wires to connect and measure using a resistive element was also implemented. Using four diodes with four discharge cycles with proper switch arrangement the resistive sensor was directly connected to the port lines of microcontroller to reject lead resistance [11]. An improved single-element resistive sensor-to-microcontroller interface was presented in [12]. With the help of single microcontroller pin, this circuit compensates the lead wire resistance using information available from three discharge cycle for computation. Here, an analog comparator through interrupt was used to limit the time of count during the discharge cycles.

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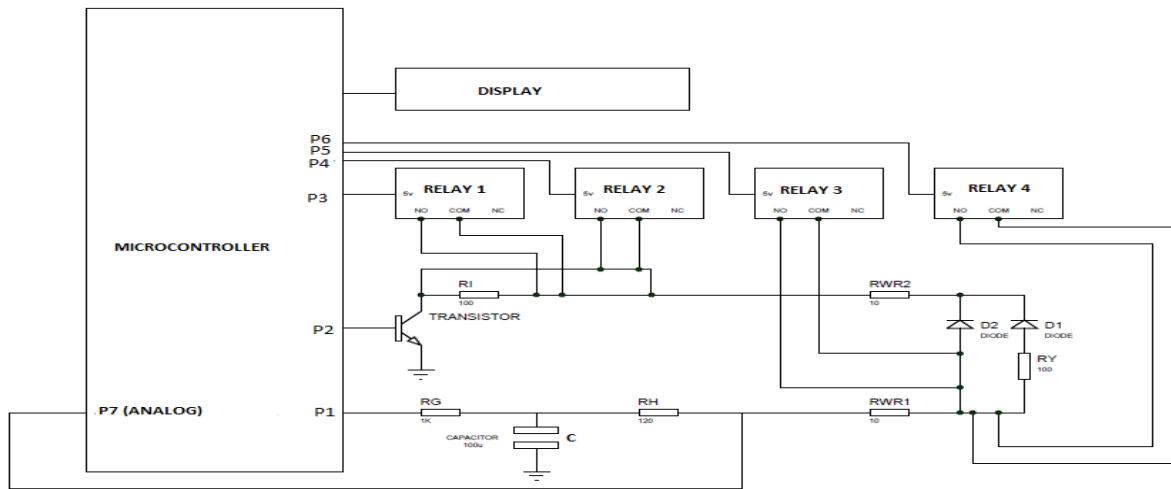
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In this proposed work, the hardware comparator is replaced by the software comparator to limit the time of count of discharge cycles and more study is made on the lead wire and port pin resistances compensation, when the resistive sensor is used as a single element. Here, the circuit complexity is also reduced by proposing a compensation technique that eliminates the error due to lead wire resistances.

### II. DESIGN OF SENSOR INTERFACING WITH MICROCONTROLLER

The circuit diagram of the proposed resistive sensor for microcontroller interfacing scheme is shown in Fig.1. The resistive sensor  $R_Y$  is connected to the measurement section using two diodes D1 and D2 and connecting wires, such as  $R_{WR1}$  and  $R_{WR2}$ . The measurement section consists of a

microcontroller, transistor, four relay switches namely, RELAY1 ( $S_1$ ), RELAY2 ( $S_2$ ), RELAY3 ( $S_3$ ) and RELAY4 ( $S_4$ ) and three resistances  $R_G$ ,  $R_H$  and  $R_I$  and a capacitor C. In the measurement process, microcontroller port pins P1-P6 (digital pins) and P7 (analog pin) are used. The port pin P1 acts as the charging pin and port pin P2 acts as the discharging pin. Port pin P7 act as internal analog comparator pin in between resistance  $R_H$  and capacitor C. Port pins P3, P4, P5, P6 are used to provide control signals for the relay and relay acts as switching device. Here, between microcontroller port pin P1 and the capacitor C, a resistor  $R_G$  is included to enhance the removal of power supply interference. Here, resistor  $R_H$  is used to make the discharge current drawn by the capacitor C to be lower than the maximum output current, when  $R_Y$  is zero.



**Fig. 1. Circuit diagram of the enhanced resistive sensor interface with microcontroller**

The nominal resistance of the sensing element is taken to be equal to the resistor,  $R_I$  connected between the two terminals of the switch. To charge the capacitor C during the charge cycle (charging pin set as HIGH) the port pin P1 is used. The port pin P2 serves as the discharging pin during the discharge cycle (discharging pin set as HIGH). In the discharging period, the discharging current of capacitor C flows through the emitter of the transistor, where the emitter is connected to the ground. Here, the measurement will be done on the basis of the three charging cycles and the three discharging cycles of the capacitor C. The charging pin P1 will be set to digitally high to charge the capacitor C till it reaches the operating voltage of the capacitor (5V) at the time of charging period of the charging cycle. The time period of the capacitor needs to be greater than  $5R_G C$  to get the capacitor C charged fully. The discharging pin P2 will be set to digitally high to discharge the capacitor operating voltage (5V) till it equals to the threshold voltage of the capacitor C (1.1V) at the discharging period of the discharging cycle. A discharge cycle follows every charge cycle.

In the first discharge cycle A, the port pin P1 acting as the charging pin is set as digitally high, the port pin P2 acting as the discharging pin is set as digitally low. Port pin P3, P5 used as relay pins are set as digitally high and port pin P4, P6 used as relay pins are set as digitally low. The relay switches  $S_1$  and  $S_3$  are at the position of normally open and the relay switches  $S_2$  and  $S_4$  are at the position of normally closed. In the discharge cycle A, diode D1 is ON and diode D2 remains

OFF. Capacitor C now discharges through resistance  $R_{Q1}$ , where

$$R_{Q1} = R_Y + R_{CP} \quad - (1)$$

$$R_{CP} = R_G + R_{WR1} + R_{WR2} + R_{PIN} + R_{SR1} + R_{SR2} + R_{SR3} + R_{SR4} \quad - (2)$$

Here,  $R_{SR1}$ ,  $R_{SR2}$ ,  $R_{SR3}$ , and  $R_{SR4}$  are the resistances of the relay switches  $S_1$ ,  $S_2$ ,  $S_3$  and  $S_4$  and  $R_{PIN}$  is the internal resistance of the microcontroller port pin P2.  $R_{WR1}$  and  $R_{WR2}$  are the lead wire resistances of the resistive sensor. The internal timer of the microcontroller gets activated at the start of the discharging cycle. When the capacitor voltage gets equal to the threshold voltage  $V_{TL}$ , the counter gets stopped. The count value  $N_A$  is the count when counter is stopped, for the time  $T_A$  for first discharge cycle. Here  $T_A = N_A T_C$  where  $T_C$  is the clock period of the microcontroller. During this period, discharge current  $i_1(t)$  is

$$i_1(t) = \frac{(V_{DD} - V_{D1})}{R_{Q1}} e^{-t/R_{Q1}C} \quad - (3)$$

Here,  $V_{D1}$  is the ON-state forward voltage drop of diode D1. The voltage,  $V_{R_{Q1}}(t)$  across  $R_{Q1}$ , can be expressed as

$$V_{R_{Q1}}(t) = i_1(t)R_{Q1} = (V_{DD} - V_{D1})e^{-t/R_{Q1}C} \quad - (4)$$

and the capacitor voltage can be stated as

$$V_C(t) = V_{DD} + V_{R_{Q1}}(t) \quad - (5)$$

By substituting  $V_{R_{Q1}}(t)$  from (4) into (5),  $V_C(t)$  becomes,

$$V_C(t) = V_{D1} + (V_{DD} - V_{D1})e^{-t/R_{Q1}C} \quad - (6)$$

The capacitor voltage,  $V_C(t)$  at  $(t = 0)$  will be

$$V_C(t) = V_{DD} \quad - (7)$$

The discharging takes place till the capacitor voltage moves down to a threshold voltage,  $V_{TL}$  hence

$$V_{TL} = V_{D1} + (V_{DD} - V_{D1})e^{-T_A/R_{Q1}C} \quad - (8)$$

Applying the natural logarithm to (8),  $T_A$  becomes

$$T_A = N_A T_c = R_{Q1} \ln \left[ \frac{V_{DD} - V_{D1}}{V_{TL} - V_{D1}} \right] \quad - (9)$$

For the considered system, if the values of  $C$ ,  $V_{DD}$ ,  $V_{TL}$ , and  $V_{D1}$  are considered to be constants, then  $T_A$  will be proportional to the total resistance  $R_{Q1}$ . Once  $T_A$  has been measured, the capacitor  $C$  is once again charged and the discharge cycle B will start.

Similarly, the time taken for discharging  $T_B$  in the second discharge cycle B is calculated as

$$T_B = N_B T_c = R_{Q2} \ln \left[ \frac{V_{DD} - V_{D2}}{V_{TL} - V_{D2}} \right] \quad - (10)$$

Here  $V_{D2}$  is the cut-in voltage of diode D2. Once  $T_B$  has been measured, the capacitor  $C$  is once again charged and the discharge cycle C will start.

Similarly, the time taken for discharging  $T_D$  in the third discharge cycle C is calculated as

$$T_D = N_D T_c = R_{Q3} \ln \left[ \frac{V_{DD} - V_{D2}}{V_{TL} - V_{D2}} \right] \quad - (11)$$

After the discharge cycle C gets completed, the capacitor  $C$  is charged again and the discharge cycle A gets started.

From the above discharge cycles, the value of  $T_A - T_D$  is calculated from (9) and (11) as

$$T_A - T_D = (N_A - N_D)T_c \quad - (12)$$

$$T_A - T_D = R_{Q1} \ln \left[ \frac{V_{DD} - V_{D1}}{V_{TL} - V_{D1}} \right] - R_{Q3} \ln \left[ \frac{V_{DD} - V_{D2}}{V_{TL} - V_{D2}} \right] \quad - (13)$$

Substituting the values of  $R_{Q1}$  and  $R_{Q3}$  in (13) and assuming that  $V_{D1} = V_{D2}$  since the diodes D1 and D2 are identical, it is found that

$$(N_A - N_D)T_c = C \ln \left[ \frac{V_{DD} - V_{D1}}{V_{TL} - V_{D1}} \right] [R_Y + R_{CP} - R_{CP}] \quad - (14)$$

Similarly, the value of  $T_B - T_D$  is calculated from (10) and (11) as

$$T_B - T_D = (N_B - N_D)T_c \quad - (15)$$

$$T_B - T_D = R_{Q2} \ln \left[ \frac{V_{DD} - V_{D2}}{V_{TL} - V_{D2}} \right] - R_{Q3} \ln \left[ \frac{V_{DD} - V_{D2}}{V_{TL} - V_{D2}} \right] \quad - (16)$$

Substituting the values of  $R_{Q2}$  and  $R_{Q3}$  in (16) and assuming that  $V_{D1} = V_{D2}$  since the diodes D1 and D2 are identical, it is found that

$$(N_B - N_D)T_c = C \ln \left[ \frac{V_{DD} - V_{D1}}{V_{TL} - V_{D1}} \right] [R_Y + R_{CP} - R_{CP}] \quad - (17)$$

Dividing (14) by (17) and rearranging,  $R_Y$  becomes,

$$R_Y = R_I \left[ \frac{N_A - N_D}{N_B - N_D} \right] \quad - (18)$$

From the equation (18), it is understood that the value of sensor is calculated from the three count values  $N_A$ ,  $N_B$  and  $N_D$  obtained during the three discharge cycles. Table 1 shows the measurement path of the three discharge cycles.

**Table 1 Measurement path of the Discharge Cycles**

Measurement Path	Microcontroller Port pin conditions						Relay switch positions				Diode Conditions		Equivalent resistance of the discharge path
	P1	P2	P3	P4	P5	P6	S1	S2	S3	S4	D1	D2	
Discharge cycle A ( $R_{Q1}$ )	H	L	H	L	H	L	NO	NC	NO	NC	ON	OFF	$R_{Q1} = R_Y + R_{CP}$
Discharge cycle B ( $R_{Q2}$ )	H	L	L	H	L	H	NC	NO	NC	NO	OFF	ON	$R_{Q2} = R_I + R_{CP}$
Discharge cycle C ( $R_{Q3}$ )	H	L	L	H	H	L	NC	NO	NO	NC	OFF	ON	$R_{Q3} = R_{CP}$

NC – Normally Closed, NO – Normally Open, H – High, L – Low

For example, if RTD is used as the resistive sensor, then  $R_Y = R_o(1 + K\theta)$  where  $\theta$  is the value of temperature being

sensed and  $K$  is the sensitivity of the RTD. Hence, by choosing  $R_I$  to be equal to nominal value  $R_o$  in (18)



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$$R_o(1 + K\theta) = R_i \left[ \frac{N_A - N_D}{N_B - N_D} \right] \quad - (19)$$

Rearranging (19)

$$\theta = \frac{1}{K} \left[ \frac{N_A - N_B}{N_B - N_D} \right] \quad - (20)$$

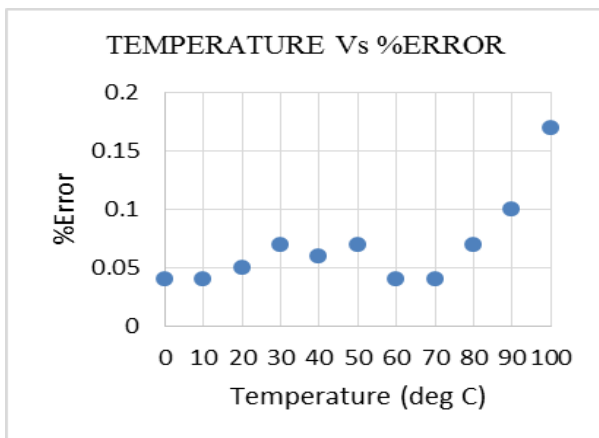
From (20) it is found that the count values  $N_A$ ,  $N_B$ ,  $N_D$  are sufficient to find the value of temperature.

### III. SIMULATION STUDY

The simulation of the circuit was done using the simulation tool, Proteus. The circuit was simulated using microcontroller, diodes, transistor and relay switches. The lead wire resistances such as  $R_{WR1}$  and  $R_{WR2}$  were set as  $10\Omega$  and the nominal resistance  $R_i$  was set as  $100\Omega$ . The sensor resistance was incremented from the temperature value of  $0^\circ\text{C}$  to  $100^\circ\text{C}$ , by increasing the temperature value in the step of  $10^\circ\text{C}$ . Here, the resistance value of  $100\Omega$  to  $139.16\Omega$  is equal to the temperature value of  $0^\circ\text{C}$  to  $100^\circ\text{C}$  for the resistive sensor RTD. The sensor resistance  $R_Y$  is calculated from the acquired three count values  $N_A$ ,  $N_B$  and  $N_D$ . It was found from simulation that the maximum error was  $0.17\%$ . Table 2 shows the comparison of the standard resistance vs measured resistance and its percentage error when proposed enhanced direct resistive sensor was interfaced with a microcontroller interface for the developed simulation study.

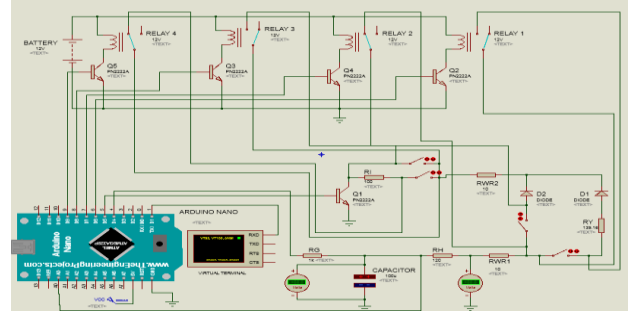
**Table 2 Simulation results for different temperature ranges**

Temperature (°C)	Standard Resistance (Ω)	Measured Resistance (Ω)	% Error
0	100	100.04	0.04
10	103.97	104.01	0.04
20	107.93	107.99	0.05
30	111.88	111.96	0.07
40	115.81	115.88	0.06
50	119.73	119.75	0.07
60	123.64	123.70	0.04
70	127.54	127.60	0.04
80	131.11	131.21	0.07
90	135.30	135.44	0.10
100	139.16	139.40	0.17



**Fig.2. Temperature vs % Error for Simulation Results**

From the graph shown in Fig. 2, it is observed that the enhanced direct resistive sensor with microcontroller interface shows a minimum error. The simulation study for the enhanced direct resistive sensor with microcontroller interface circuit was carried out using the Proteus software is shown in Fig. 3.



**Fig.3. Circuit connection taken for simulation studies**

### IV. PROTOTYPE DETAILS

While constructing the prototype, RTD (Pt100) was used as the resistive sensor and the four-channel relay RELAY1 ( $S_1$ ), RELAY2 ( $S_2$ ), RELAY3 ( $S_3$ ) and RELAY4 ( $S_4$ ) are used for the switching purpose of the three discharge cycles. The resistance values of  $R_G$ ,  $R_H$ , and  $R_i$  were selected as  $1K\Omega$ ,  $120\Omega$ ,  $100\Omega$  and the capacitance value of  $100\mu\text{F}$  was selected respectively. Two diodes (1N4007) such as D1 and D2 were selected having the same diode voltage. The switches, diodes, and resistors were connected to the microcontroller (Arduino Nano) as shown in Fig. 4. The experimental results were taken from the value of  $0^\circ\text{C}$  to  $100^\circ\text{C}$  by changing the temperature value in steps of  $10^\circ\text{C}$ . The internal comparator in the software was used to compare the threshold voltage and capacitor voltage. When the capacitor operating voltage drops from  $5V$  and equals to the threshold voltage of the capacitor  $C$  ( $1.1V$ ) at the discharging period of the discharging cycle, the counter gets stopped. For all the three discharge cycles, the time taken for the capacitor voltage to reach the threshold voltage was observed and the sensor resistance  $R_Y$  was calculated. The microcontroller was connected to the computer through the USB port to read the value of count and display the results. The experimental results are also displayed through the LCD display as shown in Fig 4.

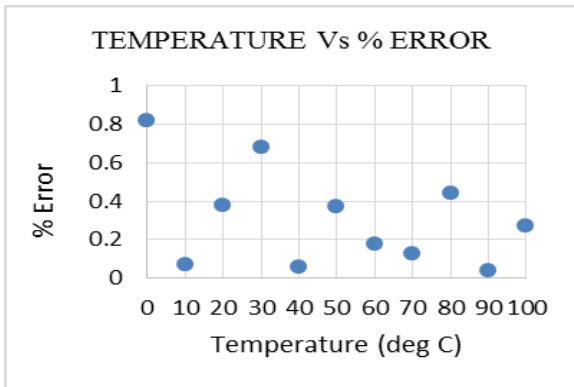


**Fig.4. Prototype Image**

Table 3 shows the comparison of the standard resistance vs measured resistance and its percentage error when proposed enhanced direct resistive sensor was interfaced with microcontroller interface for the developed prototype.

**Table 3 Prototype results**

Temperature (°C)	Standard Resistance (Ω)	Measured Resistance (Ω)	% Error
0	100	100.82	0.82
10	103.97	104.05	0.07
20	107.93	108.35	0.38
30	111.88	112.65	0.68
40	115.81	115.88	0.06
50	119.73	120.18	0.37
60	123.64	123.41	0.18
70	127.54	127.71	0.13
80	131.11	131.69	0.44
90	135.30	135.24	0.04
100	139.16	139.54	0.27



**Fig.5. Temperature vs % Error for Experimental Results**

From the graph shown in Fig 5, it is observed that the enhanced resistive sensor with a microcontroller interface scheme shows a maximum error of 0.8 % for the prototype model.

**V. CONCLUSION**

An enhanced scheme of interfacing single element resistive sensor with a microcontroller is proposed. This scheme is simple, uses low-cost components, and offers excellent accuracy during measurement. This improvement is achieved by the compensation of the lead wire resistances and the port pin resistances. The simulation studies were developed and tested using the simulation tool, Proteus. The maximum error obtained from the simulation studies is 0.17 %. A prototype circuit was developed and tested for the temperature value of 0°C to 100°C. The maximum error obtained from the prototype circuit was 0.8% and hence long lead wires can also be used for the sake of measurement, since its effect is compensated accurately.

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